

FORM PTO-1449	ATTY. DKT NO.	11-071	SER. NO.
	APPLICANT <b>TANIZAWA</b>		
	FILING DATE	November 8, 2001	GROUP

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
AD	4,576,052 (Discussed on page 2 of the spec. and corresponding to JP-B2-3-67211)	Mar. 18, 1986	Sugiyama	—	—
I	5,042,307 (Discussed on page 3 of the spec. and corresponding to JP-A-3-51733)	Aug. 27, 1991	Kato	—	—

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	TRANSLATION	
								YES	NO
AD		JP-B2-3-67211	10/22/91	JAPAN		—	—	X	
		JP-A-3-51733	3/6/91	JAPAN		—	—	X	
		JP-A-4-25767 (Corresponding to JP Patent No. 2976487 which is discussed on page 1 of the spec.)	1/29/92	JAPAN		—	—	X	
		JP-A-63-173933	7/18/88	JAPAN		—	—	X	
		JP-A-4-2170	1/7/92	JAPAN		—	—	X	
		JP-A-60-144632	7/31/85	JAPAN		—	—	X	
		JP-B2-62-55629	11/20/87	JAPAN		—	—	X	
		JP-A-3-68830	3/25/91	JAPAN		—	—	X	
		JP-A-4-89541	3/23/92	JAPAN		—	—	X	
		JP-A-57-58791	12/11/82	JAPAN		—	—	X	

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

AD	-	Sugiyama et al., "Nonlinear Temperature Characteristics in Silicon Piezoresistive Pressure Sensors," <u>Proceedings of the 5<sup>th</sup> Sensor Symposium</u> , 1985, pp.103-107.
EXAMINER	AD 46	DATE CONSIDERED 12/2/02